Journal of Electrostatics, 31 (1993) 359–360
Elsevier

Author Index Volume 31

Amerasekera, A. and A. Chatterjee, An investigation of BiCMOS ESD protection circuit elements and applications in submicron technologies 145–160
Andresen, B.H., *see* Carbajal III, B.G. 310–312
Arkhipov, V.I., D.V. Khramchenkov, A.I. Rudenko and G.M. Sessler, Space-charge dispersive transport in corona-charged dielectrics 21– 26

Bao, P.Y., *see* Matsui, M. 1– 10
Bock, K. and H.-L. Hartnagel, Fieldemitter-based ESD-protection circuits for high-frequency devices and IC's 263–279
Boudjella, A., M.Yumoto and T. Sakai, Current distributions of negative D.C. corona on the plane for point-plane gap in nitrogen rich condition 11– 19

Campbell, D.S., *see* Tunnicliffe, M.J. 91–110
Carbajal III, B.G., R.A. Cline and B.H. Andresen, A successful HBM ESD protection circuit for micron and sub-micron level CMOS 301–312
Chatterjee, A., *see* Amerasekera, A. 145–160
Chum, K., *see* Greason, W.D. 281–300
Cline, R.A., *see* Carbajal III, B.G. 301–312
Croft, G.D., On clip ESD protection using SCR pairs 177–197

Delecki, J.J., *see* Voldman, S.H. 237–262
Difaz, C., S.-M. Kang, C. Duvvury and L. Wagner, Electrical overstress (EOS) power profiles: A guideline to qualify EOS hardness of semiconductor devices 161–176
Duvvury, C., *see* Difaz, C. 161–176
Dwyer, V.M., *see* Franklin, A.J. 35– 50
Dwyer, V.M., *see* Tunnicliffe, M.J. 91–110

Fallone, B.G., *see* MacDonald, B.A. 27– 33
Franklin, A.J. and V.M. Dwyer, Electrical characterisation of ESD degradation in GaAs devices 35– 50
Fujibayashi, K., *see* Matsui, M. 1– 10

Galloway, K.F., *see* Zupac, D. 131–144
Greason, W.D. and K. Chum, Experimental study of unprotected MOS structures under EOS/ESD conditions 281–300
Gross, V.P., *see* Voldman, S.H. 237–262

Hargrove, M.J., *see* Voldman, S.H. 237–262
Hartnagel, H.-L., *see* Bock, K. 263–279
Hyatt, H.M., The resistive phase of an air discharge and the formation of fast risetime ESD pulses 339–356

Kang, S.-M., *see* Difaz, C. 161–176
Karanja, P. and R. Nath, Electrical conduction in biaxially-oriented polypropylene 51– 63
Khramchenkov, D.V., *see* Arkhipov, V.I. 21– 26
Kim, S.U., ESD induced gate oxide damage during wafer fabrication process 323–337
Kishimoto, Y., *see* Matsui, M. 1– 10
Krakauer, D., ESD protection in a 3.3 V sub-micron silicided CMOS technology 111–129

Lee, V.W., *see* Weston, H.T. 79– 89
Lin, D.L. and T.L. Welsher, From lightning to charged-device model electrostatic discharges 199–213

MacDonald, BA. and B.G. Fallone, Charge decay of electrets formed by ionizing radiation in air 27– 33
Maloney, T.J., Integrated circuit metal in the charged device model: bootstrap heating, melt damage, and scaling laws 313–321
Matsui, M., N. Murasaki, K. Fujibayashi, P.Y. Bao and Y. Kishimoto, Electrification of pure water flowing down a trough set up with a resin sheet 1– 10
Murasaki, N., *see* Matsui, M. 1– 10

Nath, R., *see* Karanja, P. 51– 63
Never, J.M., *see* Voldman, S.H. 237–262

O'Boyle, M.P., *see* Voldman, S.H. 237–262

Pote, D., *see* Zupac, D. 131–144

Rudenko, A.I., *see* Arkhipov, V.I. 21– 26

Sakai, T., *see* Boudjella, A. 11– 19
Schrimpf, R.D., *see* Zupac, D. 131–144
Scott, T.S., *see* Voldman, S.H. 237–262
Sessler, G.M., *see* Arkhipov, V.I. 21– 26
Slinkman, J.A., *see* Voldman, S.H. 237–262
Smith, D.C., Techniques and methodologies for making system level ESD response measurements for troubleshooting or design verification 215–235
Stanik, T.D., *see* Weston, H.T. 79– 89

Tunnicliffe, M.J., V.M. Dwyer and D.S. Campbell, Latent damage and parametric drift in electrostatically damaged MOS transistors 91–110

Voldman, S.H., V.P. Gross, M.H. Hargrove, J.M. Never, J.A. Slinkman, M.P. O'Boyle, T.S. Scott and J.J. Delecki, Shallow trench isolation double-diode electrostatic discharge circuit and interaction with DRAM output circuitry 237–262

Wagner, L., *see* Difaz, C. 161–176
Welsher, T.L., *see* Lin, D. L. 199–213
Weston, H.T., V.W. Lee and T.D. Stanik, A newly observed high frequency effect on the ESD protection utilized in a gigahertx NMOS technology 79– 89

Yumoto, M., *see* Boudjella, A. 11– 19

Zupac, D., D. Pote, R.D. Schrimpf and K.F. Galloway, Annealing of ESD-induced damage in power MOSFETs 131–144

Journal of Electrostatics, 31 (1993) 363
Elsevier

Subject Index Volume 31

Analysis, 161

BiCMOS, 145

Charged-device model, 199, 313
Charge decay, 27
CMOS, 111, 301
Corona, 11
Current, 51
Current distribution, 11

Damage, 131
Devices, 35
Direct damage, 313
Dispersive transport, 21
DRAM, 237

Electrets, 27
Electrical conduction, 51
EOS/ESD, 161, 281
ESD, 79, 91, 111, 131, 145, 199, 215, 237, 263, 301, 313, 323, 339
ESD degradation, 35
ESD protection, 177

Fabrication, 323
Field emission, 263

GaAs, 35, 263

High frequency, 79

Ionizing radiation, 27

Latent failures, 91

Measurement, 215, 339

NMOS, 79

Oxide damage, 323

Polypropylene, 51
Power mosfet, 131
Protection, 145, 263, 301
Protection circuit, 79, 111

Radiation-induced charge transport, 21
Reliability, 91, 145, 237

SCR, 177
Semiconductor devices, 161
Space-charge, 21

Test, 161
Thermal annealing, 131
Transients, 215

Unprotected MOS, 281

Water electrification, 1
Waveforms, 339